

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	1.35	A
		T <sub>A</sub> = +70°C		1.03	
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	6	A
Maximum Body Diode continuous Current			I <sub>S</sub>	1	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.5	W
	T <sub>A</sub> = +70°C		0.3	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	R <sub>θJA</sub>	278	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	100	nA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	μA	V <sub>GS</sub> = ±6V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.35	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	—	170	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1A
			—	230		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1A
			—	250		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 1A
Forward Transfer Admittance	Y <sub>fs</sub>	—	1.4	—	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 150mA
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	94	—	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	12	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	10	—	pF	
Gate resistance	R <sub>g</sub>	—	87.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	1.4	—	nC	V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	3.1	—	nC	
Gate-Source Charge	Q <sub>gs</sub>	—	0.13	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.14	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	4.3	—	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω, I <sub>D</sub> = 200mA
Turn-On Rise Time	t <sub>r</sub>	—	6.1	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	59.4	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	25.4	—	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

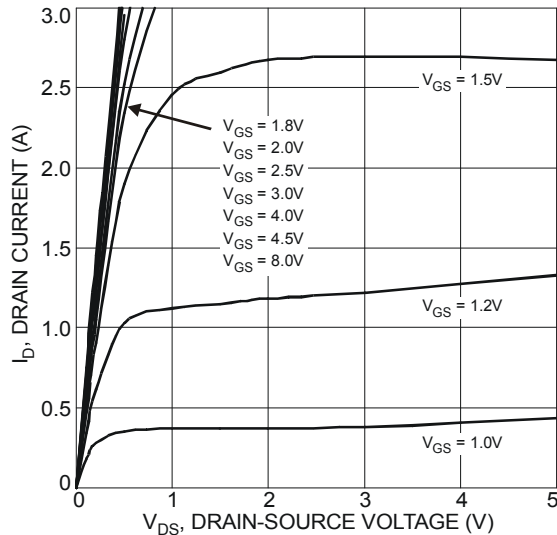


Figure 1 Typical Output Characteristic

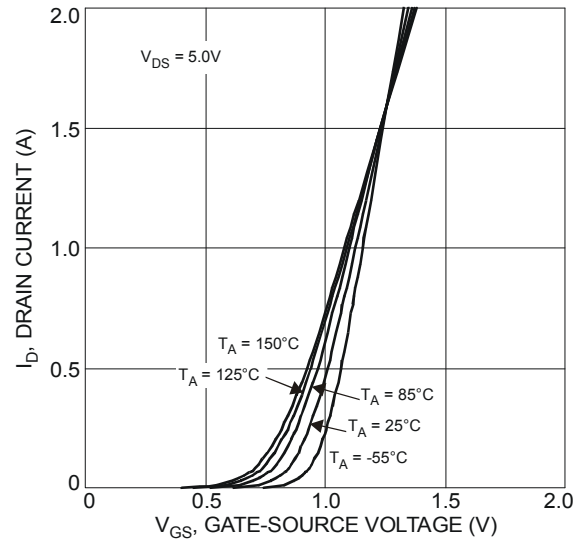


Figure 2 Typical Transfer Characteristics

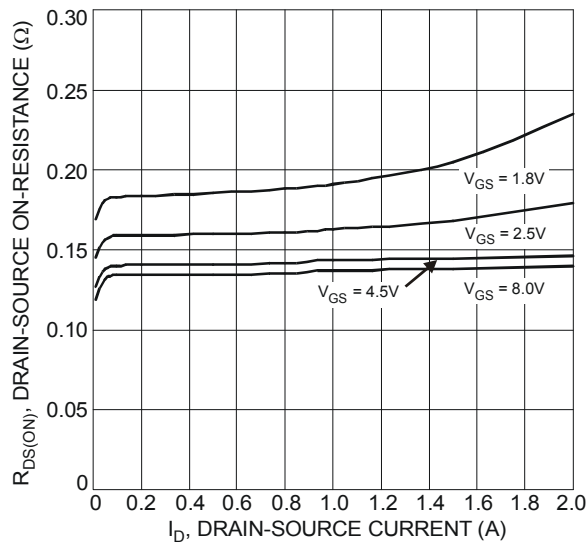


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

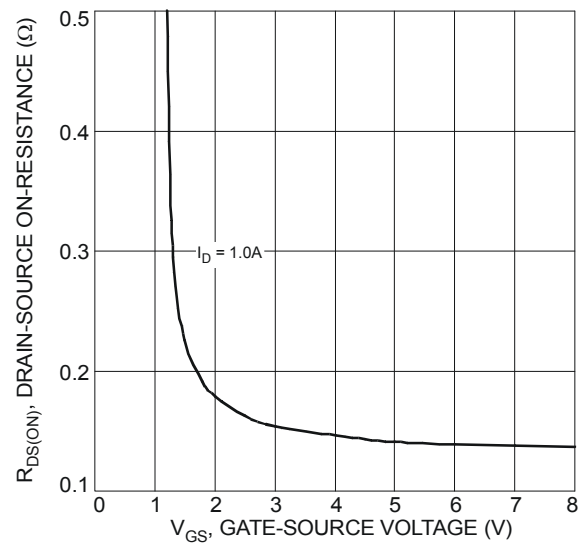


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

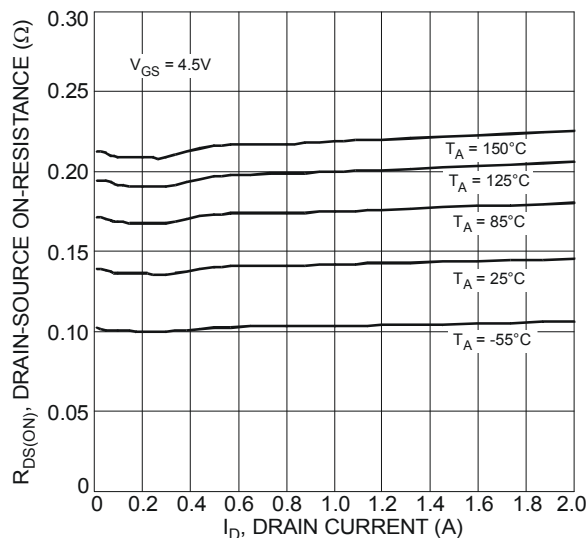


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

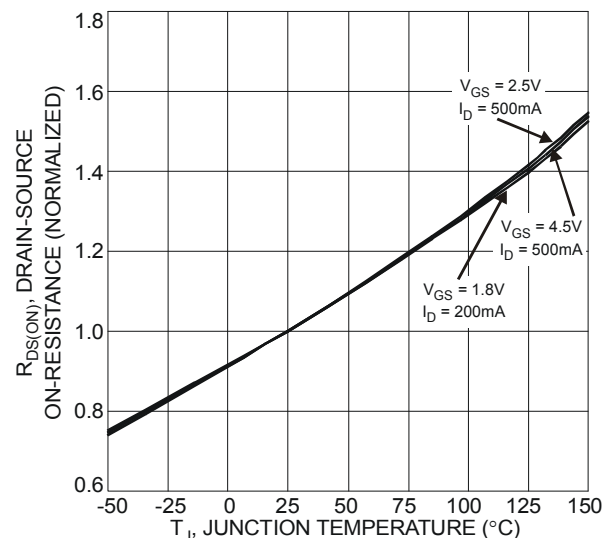


Figure 6 On-Resistance Variation with Temperature

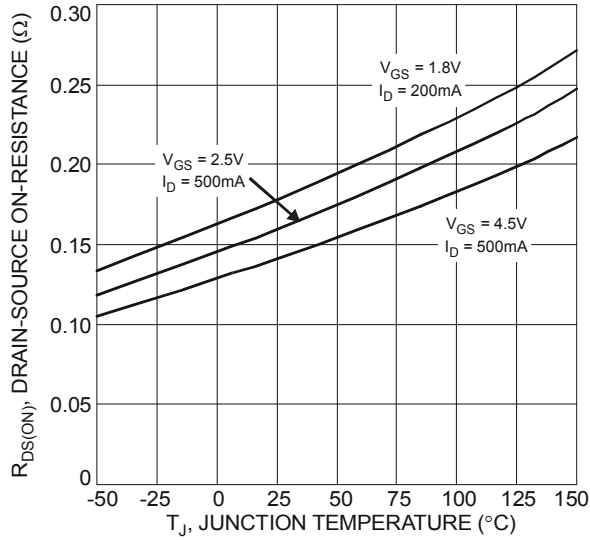


Figure 7 On-Resistance Variation with Temperature

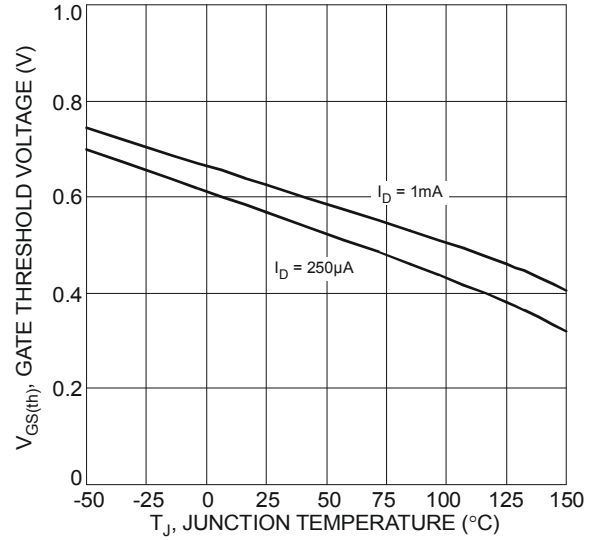


Figure 8 Gate Threshold Variation vs. Ambient Temperature

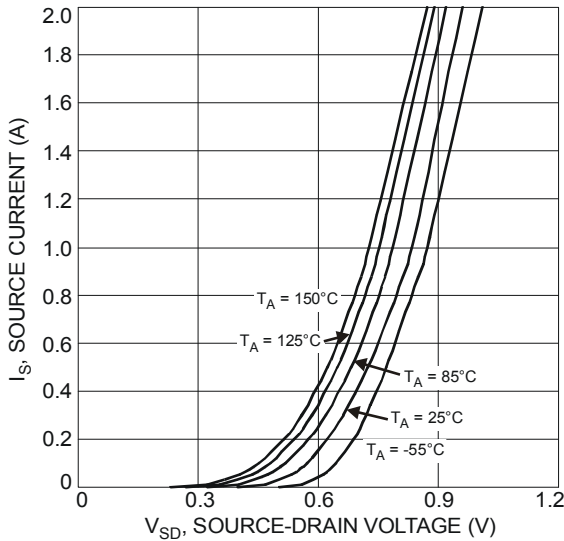


Figure 9 Diode Forward Voltage vs. Current

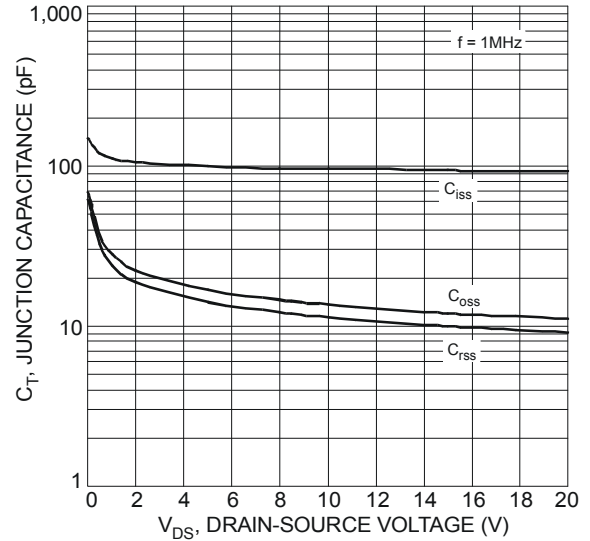


Figure 10 Typical Junction Capacitance

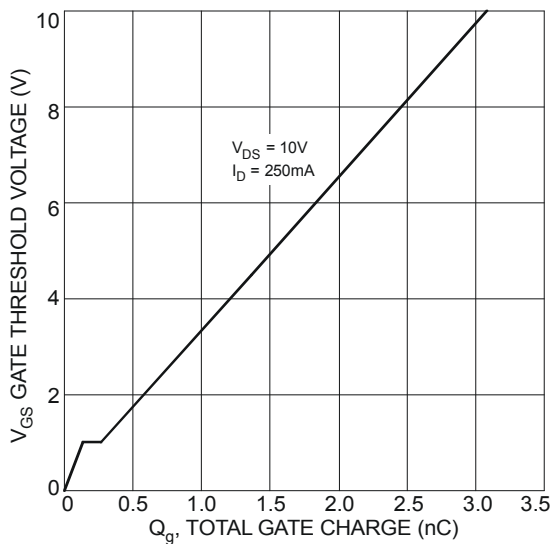
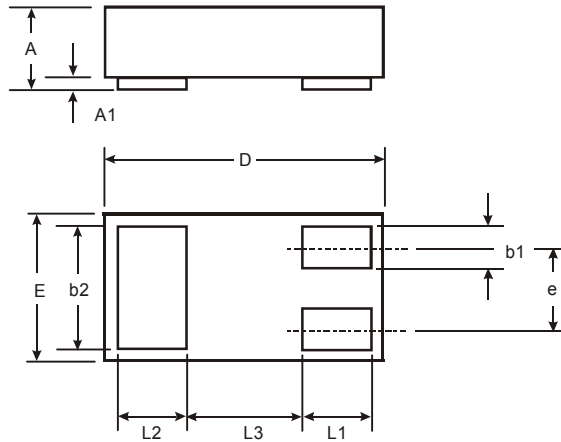


Figure 11 Gate Charge

## Package Outline Dimensions

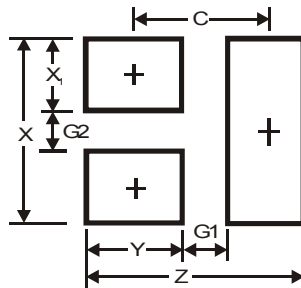
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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